L Number	Hits	Search Text	DB	Time stamp
-	3279	kraft.in.	USPAT;	2004/04/15 07:36
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	26	kraft.in. and spacers	USPAT;	2004/02/05 18:08
			US-PGPUB;	
			EPO; JPO;	İ
			DERWENT;	
			IBM_TDB	
-	42	kraft.in. and dielectric	USPAT;	2004/02/05 18:24
			US-PGPUB;	
		•	EPO; JPO;	
			DERWENT;	
			IBM_TDB	2024/22/25 12 11
-	8	(semiconductor and gate and (spacers same	USPAT;	2004/02/05 18:11
		densi\$7)) and (Xenon or Xe)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
1	1013	gemigenduator and gate and (gnagers same	IBM_TDB USPAT;	2004/02/05 18:14
-	1013	semiconductor and gate and (spacers same densi\$7)	US-PGPUB;	2004/02/03 18:14
		GCHOTA!)	EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	823	semiconductor and gate and (spacers same	USPAT;	2004/02/05 18:15
	023	densi\$7)	EPO; JPO;	2001, 02, 03 10.13
		density / /	DERWENT;	
			IBM TDB	
_	3	(semiconductor) and (spacer with (Xenon or	USPAT;	2004/04/15 07:30
		Xe))	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	5448	(semiconductor) and (spacer with	USPAT;	2004/02/05 18:27
		(implant\$3))	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	
-	3644	(semiconductor) and (spacer with	USPAT	2004/02/05 18:27
	400	(implant\$3))	******	2004/02/05 10 55
-	433	(semiconductor) and (spacer with (implant\$3)	USPAT	2004/02/05 18:57
i	1207	with (nitride or SiN or "silicon nitride"))	TTODAM.	2004/02/05 18.58
-	1397		USPAT;	2004/02/05 18:58
		(438/353)).CCLS.	US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	
_	20	(((438/404) or (438/218) or (438/294) or	USPAT;	2004/02/05 18:58
	20	((438/353)).CCLS.) and ((Xe or Xenon or Ge or	US-PGPUB;	2001, 02, 03 10.30
		Germanium) same implant\$3)	EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	35	(semiconductor) and (spacer same (Xenon or	USPAT;	2004/04/15 07:37
		(Xe))	US-PGPUB;	
1			EPO; JPO;	
			DERWENT;	· ·
			IBM TDB	
[-	226	spacer same (Xenon or Xe)	USPAT;	2004/04/15 07:37
			US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
<u> </u>			IBM_TDB	
] -	11	(spacer same (Xenon or Xe)) and ("integrated	USPAT;	2004/04/15 07:39
1		circuit" or IC)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	·
			IBM_TDB	

-	3400	spacer with stress	USPAT;	2004/04/15 07:39
			US-PGPUB; EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	78	(spacer with stress) and (Xenon or Xe)	USPAT;	2004/04/15 07:40
		(100001 11000 10000) 01100 (1101001 01 110)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM_TDB	•
-	22		USPAT;	2004/04/15 07:44
		(semiconductor or "integrated circuit" or	US-PGPUB;	
		IC)	EPO; JPO;	
			DERWENT;	
† -	7914	 semiconductor and (spacer near (film or	IBM_TDB USPAT;	2004/04/15 07:45
-	/914	layer))	US-PGPUB;	2004/04/15 07:45
		Tayer, /	EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	48	(semiconductor and (spacer near (film or	USPAT;	2004/04/15 14:17
		layer))) and ((germanium or Ge or xenon or	US-PGPUB;	
	1	Xe) near (ion or atom))	EPO; JPO;	
			DERWENT;	
			IBM_TDB	0004/04/47
-	49128	(selectiv\$3 or etch\$3) with (nitride or SiN)	.USPAT;	2004/04/15 14:19
		·	US-PGPUB;	
			EPO; JPO; DERWENT;	
			IBM TDB	
_	624	(selectiv\$3 or etch\$3) with (nitride or SiN)	USPAT;	2004/04/15 14:22
		same (Xe or Ge or Xenon or Germanium)	US-PGPUB;	2001, 01, 10 21122
}		,	EPO; JPO;	
			DERWENT;	·
			IBM_TDB	
-	70	(selectiv\$3 near etch\$3) with (nitride or	USPAT;	2004/04/15 14:36
		SiN) same (Xe or Ge or Xenon or Germanium)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	1088	(selectiv\$3 near etch\$3) with (nitride or	IBM_TDB USPAT;	2004/04/15 14:36
-	1088	SiN) same (ion or atom)	US-PGPUB;	2004/04/15 14.30
		BIN, Bame (1011 Of acom)	EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	58	(selectiv\$3 near etch\$3) with (nitride or	USPAT;	2004/04/15 15:44
		SiN) same ((ion or atom) with (implant\$3))	US-PGPUB;	
1		same spacer	EPO; JPO;	
			DERWENT;	
	1	//#4010714#\ @@ (#5507751#\ @@ (#5714430#\	IBM_TDB	2004/04/15 15:40
-	17	(("4818714") or ("5597751") or ("5714412") or ("5766988") or ("5789296") or ("5811853")	USPAT	2004/04/15 15:48
		or ("5/66988") or ("5/89296") or ("5811853") or ("5858840") or ("5872036") or ("5909622")		
		or ("5970371") or ("6001690") or ("6031264")		
		or ("6140182") or ("6165845") or ("6166405")		
		or ("6184088") or ("6187657")).PN.		
-	333	(selectiv\$3 near etch\$3) with (nitride or	USPAT;	2004/04/15 16:05
		SiN) same ((ion or atom) with (implant\$3))	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
		and an with (Co or comment) and (cot-	IBM_TDB	2004/06/11 14:52
-	87	spacer with (Ge or germanium) and (gate near electrode)	USPAT; US-PGPUB;	2004/06/11 14:52
		erectione)	EPO; JPO;	
			DERWENT;	
			IBM TDB	
-	522	(germanium or Ge) near (implant\$3)	USPAT;	2004/06/11 14:52
		•	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
	1		IBM_TDB	

-	36	((germanium or Ge) near (implant\$3)) same		2004/06/11 14:53
		(spacer or spacers)	US-PGPUB;	j
			EPO; JPO;	
			DERWENT;	
	ļ		IBM TDB	
_	13	((germanium or Ge) near (implant\$3)) with	USPAT; 2	2004/06/11 14:57
	•	(spacer or spacers)	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	0	((Xenon or Xe) near (implant\$3)) with		2004/06/11 14:57
	_	(spacer or spacers)	US-PGPUB;	,,
		(Spacer or Spacer)	EPO; JPO;	
			DERWENT;	
			IBM TDB	,
1_	5	((Xenon or Xe) near (implant\$3)) same		2004/06/11 15:16
		(spacer or spacers)	US-PGPUB;	3001,00711 13:10
		(Spacer of Spacers)	EPO; JPO;	
		·	DERWENT;	
			IBM TDB	
_	742	(implant\$3) near (spacer or spacers)		2004/06/11 15:18
_	742	(limprances) hear (spacer or spacers)	US-PGPUB:	1004/00/11 13:18
			EPO; JPO;	
			DERWENT;	
			IBM TDB	
	439	(implant\$3) near (spacer or spacers) and		2004/06/11 15:18
-	439	semiconductor	· ·	2004/06/11 15:18
		semiconductor	US-PGPUB;	
			EPO; JPO;	
			DERWENT;	
		/#4060407# #4100700#	IBM_TDB	004/06/11 15 50
-	29	("4060427" "4102733" "4272880"	USPAT 2	2004/06/11 15:59
		"4298629" "4330931" "4382827"		
		"4402761" "4455742" "4512074"		
		"4542580" "4589936" "4621277"		
		"4623912" "4629520" "4715937"		
		"4775642" "4835112" "5093700"		
		"5168072" "5180690" "5266514"		
		"5276347" "5326722" "5600166"		
		"5683929" "5792690" "5915182"		
	_	"5969397" "6015740").PN.		
	1	6331468.URPN.	USPAT 2	004/06/11 16:02